



Description

The DMP2170U uses advanced trench technology to provide excellent $R_{DS(ON)}$. This device is suitable for use as a load switch or in PWM applications.



SOT-23

General Features

$V_{DS} = -20V$, $I_D = -3A$

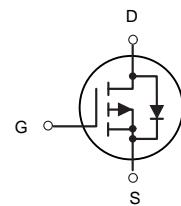
$R_{DS(ON)} < 80m\Omega$ @ $V_{GS} = -4.5V$

Application

Battery protection

Load switch

Uninterruptible power supply



P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
DMP2170U	SOT-23	HXY MOSFET	3000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Drain Current-Continuous	-3	A
I_{DM}	Drain Current-Pulsed (Note 1)	-10	A
P_D	Maximum Power Dissipation	1	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	125	°C/W



Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-20	-24	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=-20\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	μA
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 12\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-0.4	-0.7	-1	V
Drain-Source On-State Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-3\text{A}$	-	60	80	$\text{m}\Omega$
		$V_{\text{GS}}=-2.5\text{V}, I_{\text{D}}=-2\text{A}$	-	85	103	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{\text{DS}}=-5\text{V}, I_{\text{D}}=-2\text{A}$	5	-	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{\text{DS}}=-10\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	405	-	PF
Output Capacitance	C_{oss}		-	75	-	PF
Reverse Transfer Capacitance	C_{rss}		-	55	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{\text{d(on)}}$	$V_{\text{DD}}=-10\text{V}, I_{\text{D}}=-1\text{A} V_{\text{GS}}=-4.5\text{V}, R_{\text{GEN}}=10\Omega$	-	11	-	nS
Turn-on Rise Time	t_{r}		-	35	-	nS
Turn-Off Delay Time	$t_{\text{d(off)}}$		-	30	-	nS
Turn-Off Fall Time	t_{f}		-	10	-	nS
Total Gate Charge	Q_{g}	$V_{\text{DS}}=-10\text{V}, I_{\text{D}}=-3\text{A}, V_{\text{GS}}=-2.5\text{V}$	-	3.3	12	nC
Gate-Source Charge	Q_{gs}		-	0.7	-	nC
Gate-Drain Charge	Q_{gd}		-	1.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{\text{GS}}=0\text{V}, I_{\text{s}}=1.3\text{A}$	-	-	-1.2	V
Diode Forward Current (Note 2)	I_{s}		-	-	-3	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

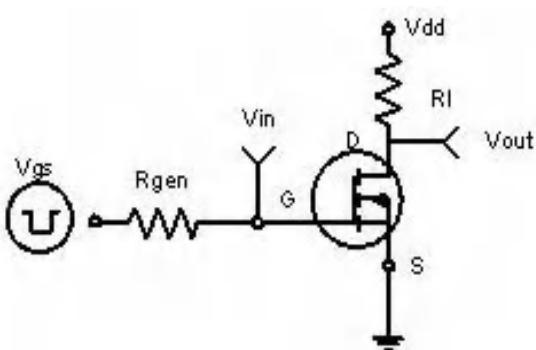


Figure 1:Switching Test Circuit

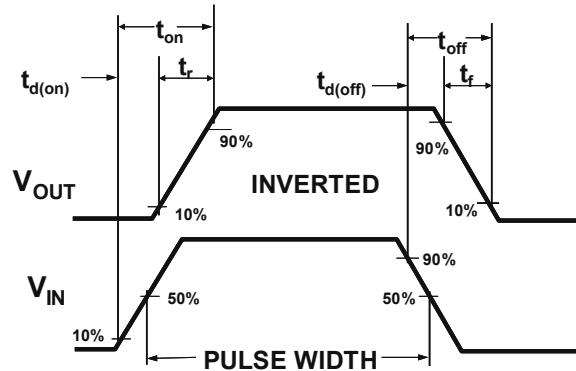
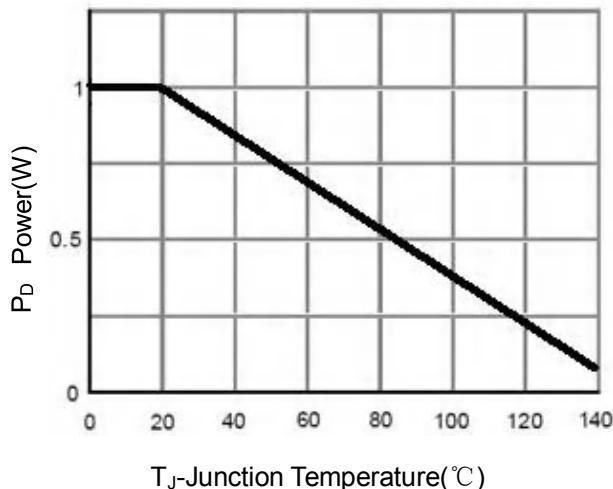
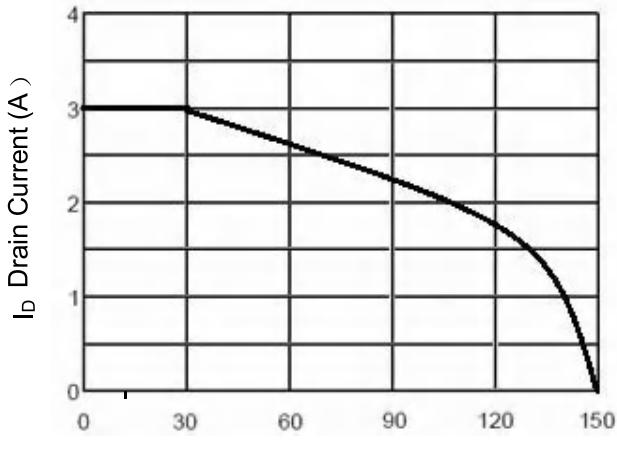


Figure 2:Switching Waveforms



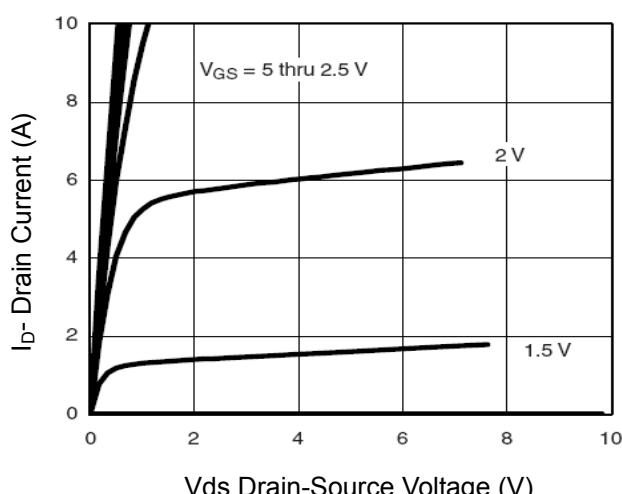
T_J-Junction Temperature(°C)

Figure 3 Power Dissipation



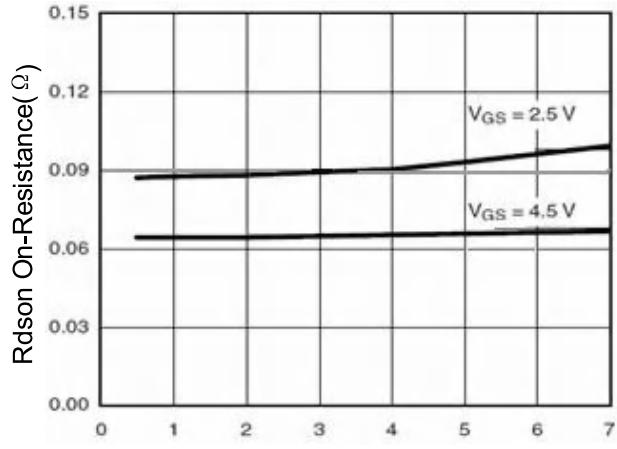
T_J-Junction Temperature(°C)

Figure 4 Drain Current



Vds Drain-Source Voltage (V)

Figure 5 Output Characteristics



ID- Drain Current (A)

Figure 6 Drain-Source On-Resistance

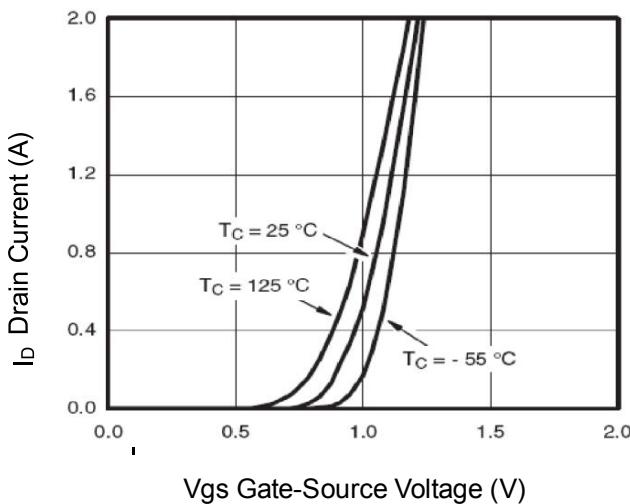


Figure 7 Transfer Characteristics

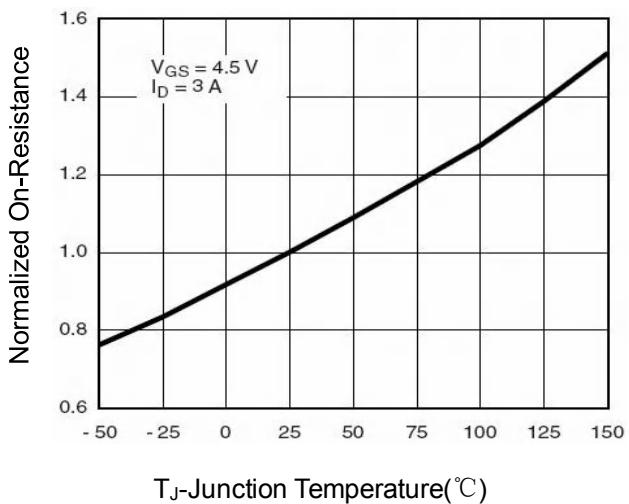


Figure 8 Drain-Source On-Resistance

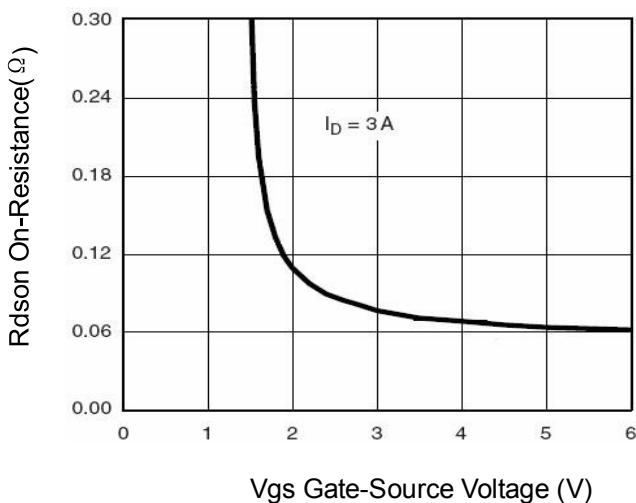


Figure 9 $R_{DS(on)}$ vs V_{GS}

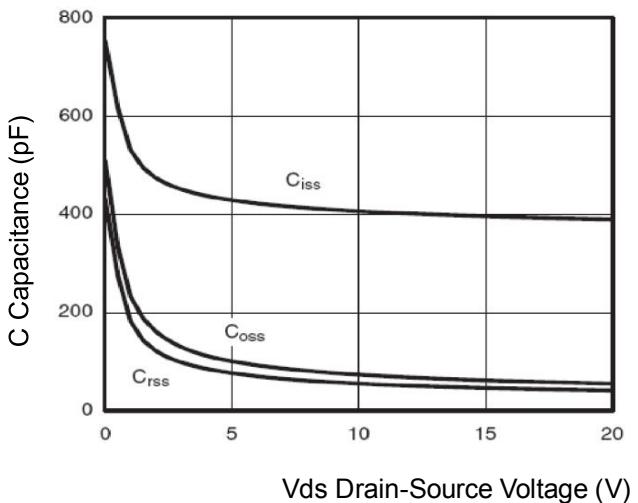


Figure 10 Capacitance vs V_{DS}

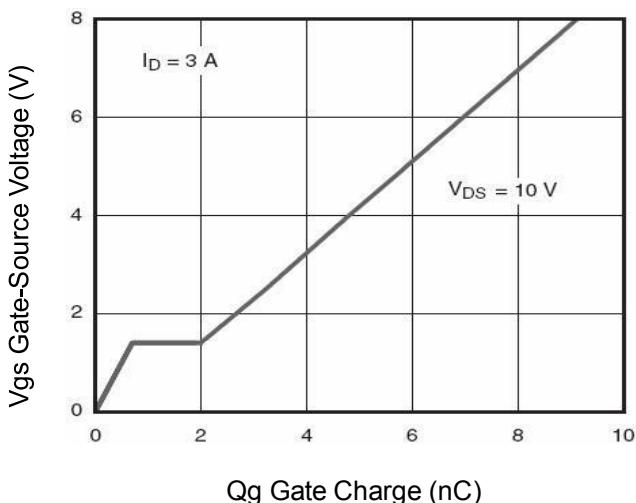


Figure 11 Gate Charge

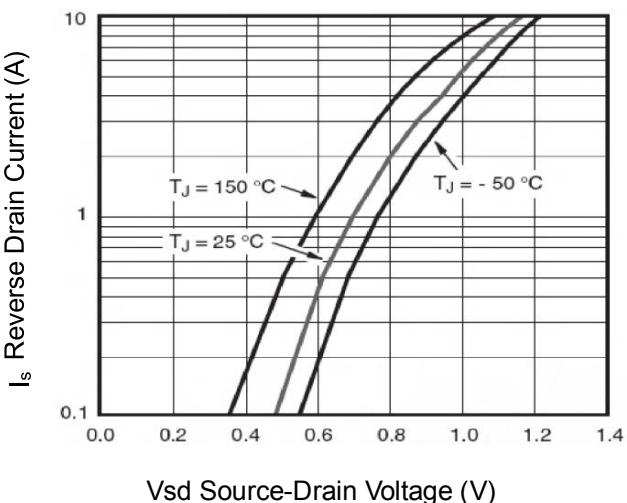


Figure 12 Source-Drain Diode Forward

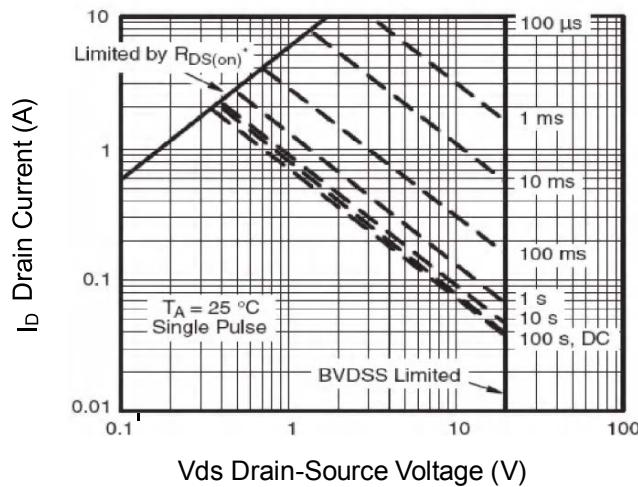


Figure 13 Safe Operation Area

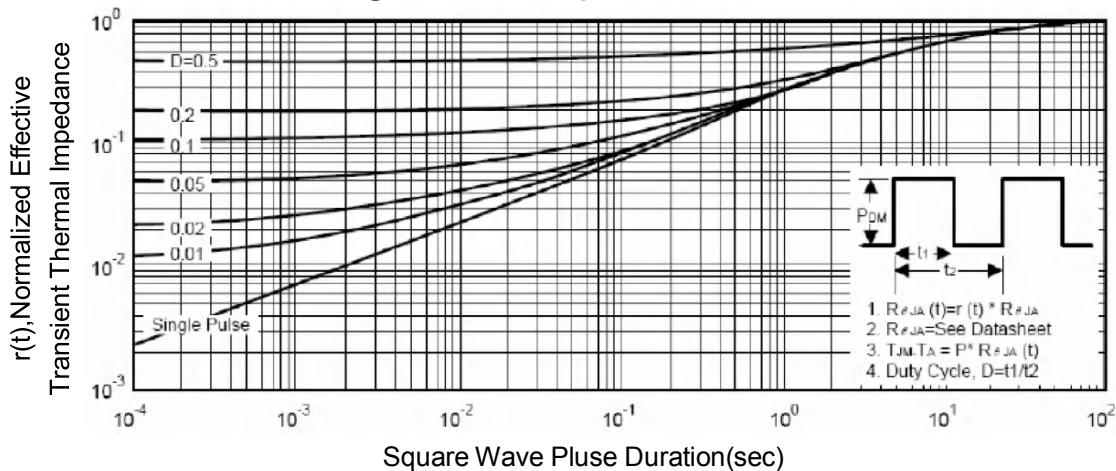
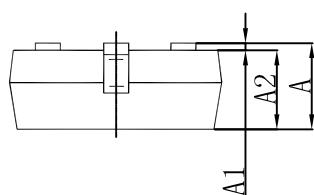
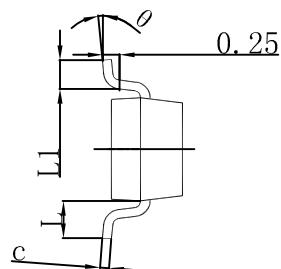
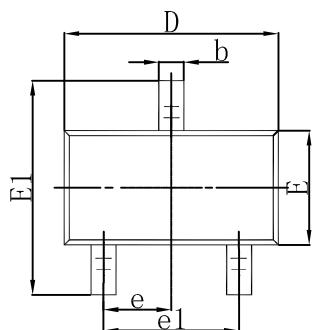


Figure 14 Normalized Maximum Transient Thermal Impedance

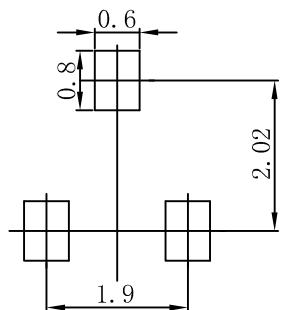


SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.



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